

ABSTRACT OF THE DISCLOSURE

The present invention relates to a CMOS-type solid-state imaging device and a method for manufacturing thereof, and provides a solid-state imaging device capable of optimally condensing light by a single intra-layer lens and a manufacturing method capable of forming an intra-layer lens with high precision.

The solid-state imaging device according to the present invention includes a plurality of wirings and a plurality of lenses above a light-receiving portion, in which at least one of the plurality of lenses is formed of a single intra-layer lens.

The method for manufacturing the solid-state imaging device according to the present invention includes the processes of forming a concave surface or convex surface onto a first insulation layer with a first refractive index using a selective etching method and forming a second insulation layer with a second refractive index onto the concave surface or convex surface to form the intra-layer lens corresponding to the light-receiving portion.